/ Descriptions

TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

/ Features

P_C,I_C , 8550

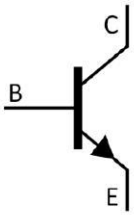
High P_C and I_C, complementary pair with 8550.

/ Applications

2W

2W output amplifier of portable radios in class B push-pull operation.

/ Equivalent Circuit



/ Pinning



PIN1 Collector PIN 2 Base PIN 3 Emitter

/ h_{FE} Classifications & Marking

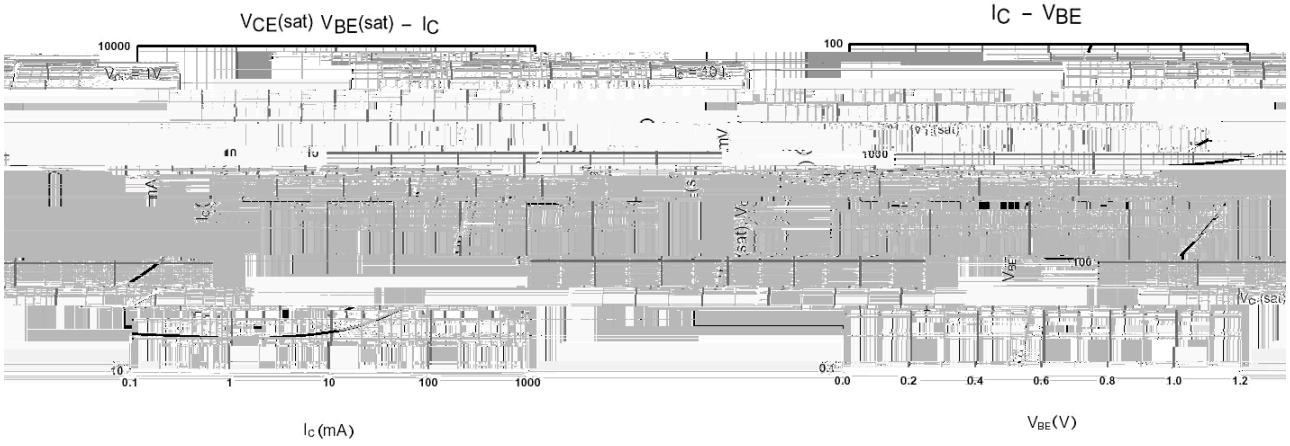
h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	85~160	120~200	160~300

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current - Continuous	I_C	1.5	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

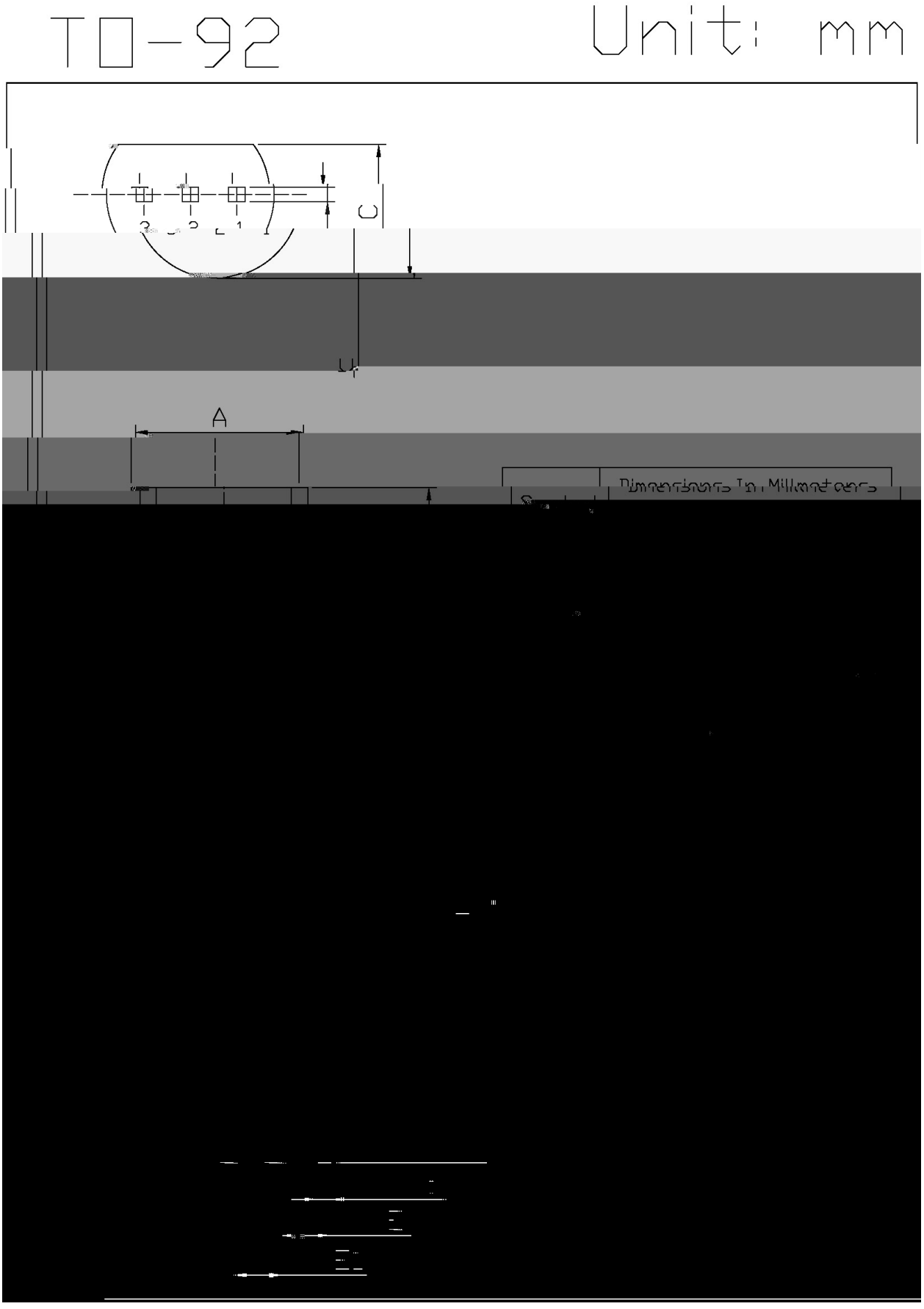
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.1mA I_E=0	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=2.0mA I_B=0	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=0.1mA I_C=0				

/ Electrical Characteristic Curve

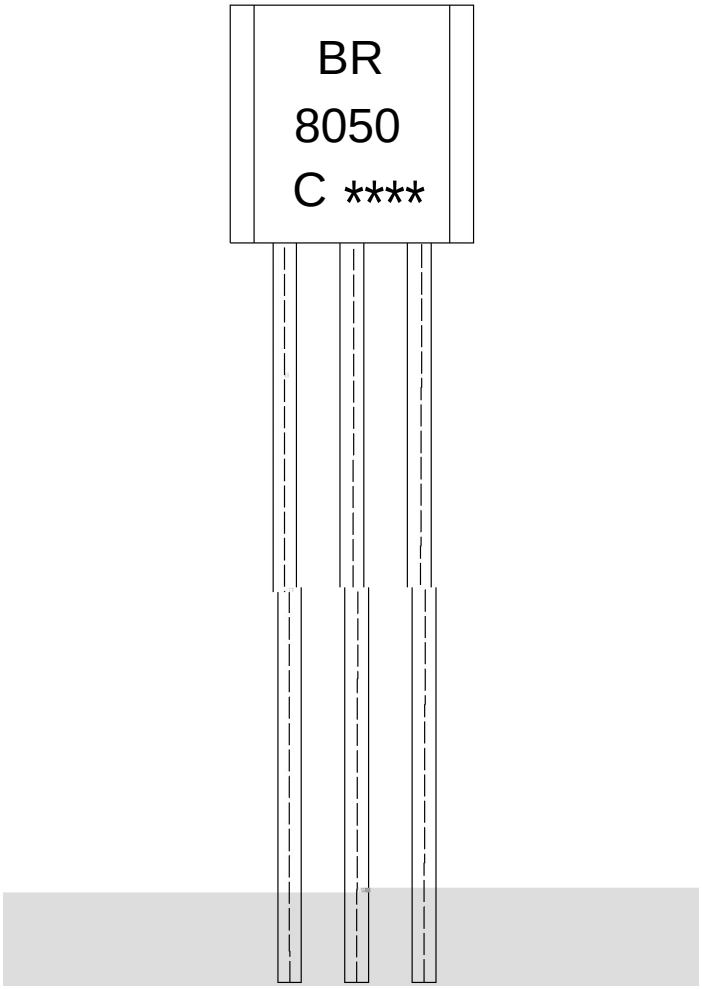




/ Package Dimensions



/ Marking Instructions



BR

8050

C: h_{FE}

****

Note:

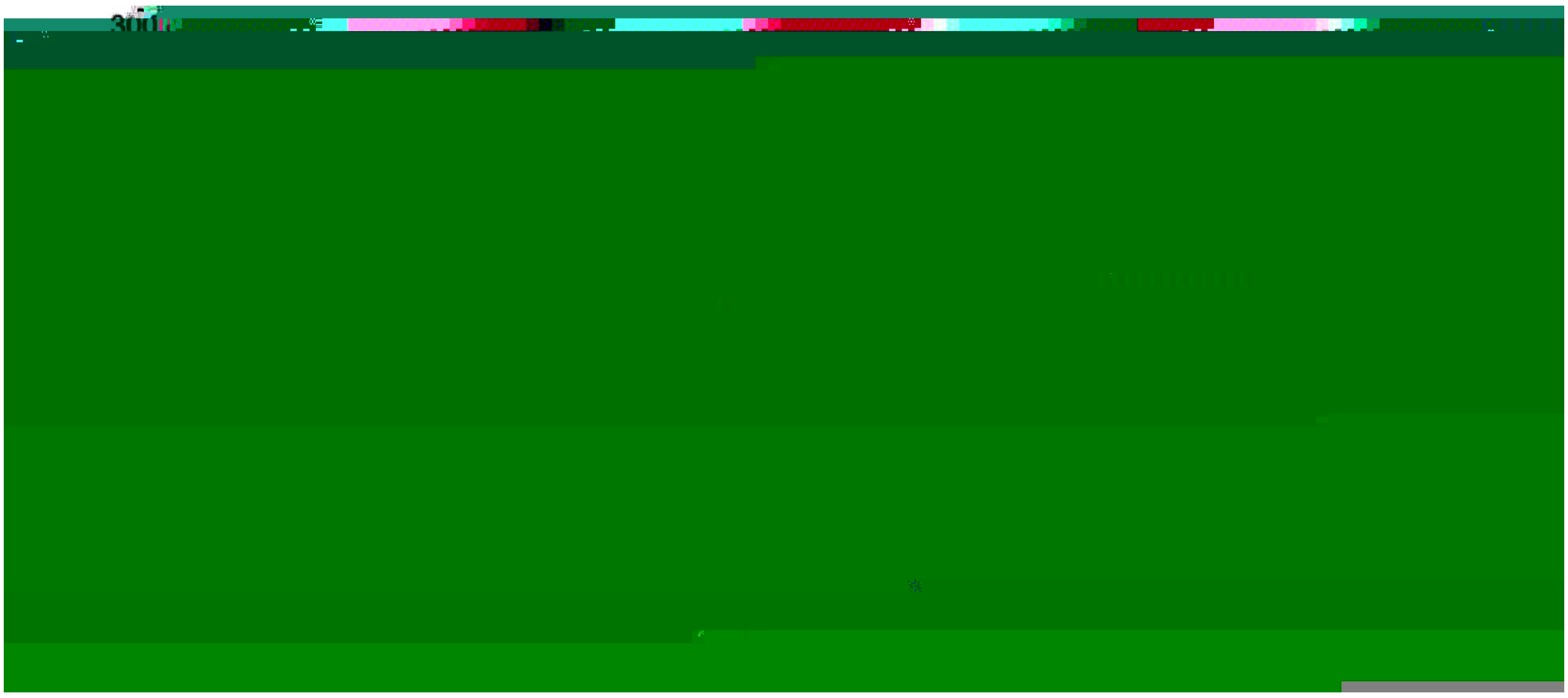
BR: Company Code.

8050: Product Type.

C: h_{FE} Classifications Symbol.

****: Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK